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碩士論文

在多核心系統中考慮動態隨機存取記憶體讀/寫特性 以降低功率消耗之排程機制 A Read-Write Aware DRAM Scheduling for Power Reduction in Multi-Core Systems

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近幾年來,隨著市場及業界對於高效能、低功耗系統的需求,功耗管理的重要性已 日漸增加。在現今的多核心系統當中,動態隨機存取記憶體(DRAM)的功率消耗佔了整 個系統的一大部分,因此吸引了許多人研究 DRAM 的功耗管理。而除了功率消耗之外, DRAM 同時還是目前多核心系統中的效能瓶頸,所以在設計 DRAM 功耗管理的方法時, 必須格外地小心以避免大幅度地降低系統效能。目前關於 DRAM 功耗管理方法的研究 中,有大量的研究是透過 DRAM 的排程機制來排序指令以降低功率消耗。在此基礎上, 本篇論文提出考慮 DRAM 讀/寫特性的指令調節技術以及指令排程機制,在不影響系統 效能的前提下,進一步降低 DRAM 功率消耗。根據實驗結果,本篇論文提出的機制平 均能夠有效降低 75%的 DRAM 功率消耗。若與現有的方法比較,本篇論文所提出的機 制能夠在相同甚至是較少的系統效能損失之下,多降低 10%的 DRAM 功率消耗。

A Read-Write Aware DRAM Scheduling for Power

Reduction in Multi-Core Systems

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ABSTRACT

The demand of high performance and low power has increased the importance of power efficiency in multi-core systems. In modern multi-core architectures, DRAM has dominated the power consumption. Moreover, the performance of nowadays system is limited by the memory wall, which implies that a careless DRAM power management policy may harm the system performance dramatically. Among all the DRAM power management policies, reordering based DRAM scheduling has been widely studied to reduce the power. To further reduce the power while preserving the system performance, this thesis proposes the read-write aware throttling and the read-write reordering techniques. The proposed techniques effectively reduce 75% DRAM power on average. When compared to the existing work, the proposed techniques reduce 10% more power with comparable or less performance degradation on average.

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Chapter 1 Introduction

In the latest multi-core systems, the increasing performance comes at the cost of the higher power consumption [1]. Within a multi-core architecture, it has been shown that main memory contributes up to 40% of the system power consumption [2][3][4]. For large scale systems such as datacenter, this fraction increases along the growing demand of memory capacity [5][6][7]. As the result, reducing the power consumption of main memory has become the main issue for chip designers.

Among existing memory circuits, *dynamic random access memory* (DRAM) is by far the mainstream of main memory used in modern multi-core systems. Hence, this thesis focuses on reducing the DRAM power consumption. To generalize the discussion, this thesis chooses to work on the widely used JEDEC standard DRAM architectures [8].

1.1DRAM Architecture

Fig. 1 illustrates the architecture of a JEDEC standard DRAM. The JEDEC standard DRAM is composed of multiple *dual-in-line memory modules* (*DIMMs*), in which multiple DRAM chips are put together to provide a wide data interface. Sets of DRAM chips lie in a DIMM. Each set of these DRAM chips is called a *rank*. Each rank can be further partitioned into *banks*, which spread across all DRAM chips within a rank. Each bank is organized as a two-dimensional array and its size is defined as *rows* × *columns*. Only a single row of data can be accessed at any given time. Each bank has its own *row buffer* to store the row of data that is ready to be accessed [9]. Since the DRAM is a volatile memory, the data stored in the array need to be periodically refreshed to prevent data loss.



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DRAM chip
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Fig. 1 The architecture of a DIMM, which includes ranks and banks, inside the DRAM.

The DRAM is operated by two types of commands, the internal commands and the request commands. The internal commands includes *refresh*, *activate* (*ACT*), *precharge* (*PRE*), *power-down* and *power-up*. All the internal commands are generated inside the DRAM. On the other hand, the request commands are the commands sent to the DRAM by the processor. A request command contains its access type and a target address indicating its target rank and target bank. Write request commands further contain the data to be written into the DIMMs. For simplicity, in the remainder of this thesis, the term *memory command* refers to the memory request command if not specified.

For a memory command to access a location in the DIMMs, several internal commands are triggered to carry out the read or write request. First, all the DRAM chips in the target rank of the memory command need to be activated. The DRAM generates an ACT command and sends it to the target bank of the memory command. The ACT command activates all the DRAM chips in the bank and reads out an entire row of data. This row of data is stored in the row buffer. The data can either be read from or written to a column, which is indicated by the memory command, inside the fetched row. After the request completes, the DRAM send a PRE command to the open bank. The PRE command restores the data from the row buffer to the memory array inside the bank [10]. Fig. 2 shows an example of how a sequence of continuous read commands to the same row are carried out inside a DRAM bank.



inside a DRAM bank.

The DIMMs communicates with the processors through the *memory controller*, which is planted in the DRAM. The memory controller sits in between the last level cache and the DIMMs. It receives memory commands from the processor, and maps the addresses in the received commands to their target ranks and target banks inside the DIMMs. The memory controller then issues the received memory commands to the DIMMs. The memory controller is able to reorder the memory commands while preventing data hazards. The memory controller is also in charge of generating the internal commands such as ACT, PRE, and refresh. The memory controller can switch the power mode of a rank by generating power-down or powerup commands.

The master operation of a DRAM chip is controlled by the corresponding *clock enable* (*CKE*) signal. When CKE is low, all inputs, including DRAM clocks, are disabled [11]. If the

CKE for a DRAM chip is low, that DRAM chip is considered to be in the *off* mode. None of the request commands or the internal commands can be processed by a DRAM chip when it is in the off mode. The only exception is the refresh command. Even when a DRAM chip is in the off mode, it has to be periodically refreshed in order to retain data integrity in itself. The DRAM clocks start propagating through a DRAM chip when the CKE is risen to high. The DRAM chip begins taking inputs and processes the received memory commands. The DRAM chip is considered to be in the *on* mode when the CKE is high.



1.2 Reducing the DRAM Power

The power consumption of the DRAM consists of several different components. First of all, the DRAM continuously consumes a background power. The value of the background differs from the mode of the DRAM chip. When the DRAM chip is in the off mode, the background power is defined to be P_{PDN} . The background power is defined to be P_{ACT_STBY} when the DRAM chip is in the on mode. It is natural that P_{ACT_STBY} is larger than P_{PDN} ; for modern DRAM circuits, P_{PDN} is just 6.67%~15.38% of P_{ACT_STBY} [10][11]. The periodic refresh operation consumes the refresh power (P_{REF}). Finally, active power (P_{ACT}), precharge power (P_{PRE}), and the read or write power (P_{RD} or P_{WR}) are average power needed for all memory accesses. To sum up, the power consumptions of the DRAM can be written as:

$$P_{off} = P_{PDN} + P_{REF}$$

$$P_{on} = P_{ACT_STBY} + P_{REF} + P_{ACT} + P_{RD} + P_{WR} + P_{PRE},$$

$$(1)$$

where P_{off} and P_{on} represent the power consumption of DRAM chips in the off mode and on mode respectively. The power consumption of DRAM chips in the off mode is the lowest power in which DRAM chips may keep the data integrity, and the off mode is therefore known as the *low power* mode.

Since the DRAM chips consume less power when they are in the low power mode, the DRAM chips that are idle should be turned off in order to reduce the DRAM power. Due to the fact that all the DRAM chips inside a rank need to be activated for a memory access, it is impossible to turn off a single DRAM chip alone. Therefore, a rank is the smallest set of DRAM chips that can be turned off. The JEDEC standard DRAM supports rank level power mode control and allows users to turn on or turn off each rank separately [8][12].

Although turning off idle ranks reduces the DRAM power, switching power mode of a rank takes a transition delay of time. Fig. 3 illustrates the power mode transition delays between two memory accesses, which can either be read or write (R/W). In Fig. 3, the memory accesses are depicted as rectangles, whereas t_{PDN} and t_{PUP} represent power-down transition delay and power-up transition delay respectively. The delays of switching power mode of ranks bring extra latencies to the system performance. Therefore, one of the main goals for designing DRAM power reduction techniques is to design a policy that determines when to turn on and off DRAM ranks. An immature policy leads to loss of power saving or serious degradation to the system performance.



1.3 Related Works and Motivation

Many different types of approaches toward DRAM power reduction have been studied in recent years. These approaches include designing a hybrid main memory, re-designing the physical structure of the DRAM, adding hardware component to the DRAM and designing power management policy for the memory controller in the modern DRAM.

Designing a hybrid main memory aims to reduce the DRAM power consumption by cutting down the refresh energy consumed by the DRAM. Phase change random access memory (PCRAM) is used in the hybrid memory as a large background main memory since it consumes low standby power. The DRAM serves as a cache above PCRAM [13][14]. The data in DRAM decay over time and are written back to the PCRAM if they are dirty. The DRAM refresh energy is thus reduced. Besides integrating PCRAM with DRAM, some proposed to use the cached DRAM, which adds a cache directly into the memory device [15]. Adding cache to the DRAM reduces the access to DRAM chips and thus increases the idle period. Therefore, the DRAM chips can be put to the low power mode to save more power.

Re-designing the physical structure of DRAM targets to improve the granularity of DRAM power mode control, which increases the potential of turning off idle DRAM chips. Some proposed to separate ranks into mini-ranks by adding mini-rank buffers inside each rank [16]; others proposed to change the arrangement of arrays in each bank [2]. These approaches allow the memory controller to switch the power mode of a set of DRAM chips, which the number of chip is smaller than that contained in a rank. It is more likely for DRAM chips in a smaller chip set to be all idle. Therefore, the memory controller has more chance to turn off idle chips and thus reduces the DRAM power consumption.

Both designing hybrid main memories and re-designing the physical structure of the DRAM have the potential to achieve good performance. Nevertheless, they both require big modifications to the modern DRAM architecture. Since this thesis aims to design power

reduction techniques for DRAMs that are commonly used in nowadays multi-core systems, these approaches are not suitable.

A different type of approaches reduce the DRAM power by adding some extra hardware to the existing DRAM circuit and extend its capability. For example, retention-aware intelligent DRAM refresh mechanism identifies and skips unnecessary refreshes for the DRAM [17]. By only refreshing necessary rows in DRAM banks, the refresh power is cut down. Another example is automatic data migration, which migrates data from ranks to ranks and tries to make the memory access concentrate on certain ranks [18]. This creates more empty ranks, which do not need to be periodically refreshed and can be completely shut off for a period of time. However, these approaches require a large hardware overhead to implement.

In order to reduce the DRAM power consumption without a big modification to the modern DRAM circuits, many approaches design power management policies for the memory controllers. The policies can be categorized into power-down policies, which determine when to turn an idle rank off; scheduling policies, which schedule the commands in the memory controller; throttling-based policies, which block command in the buffer to prolong the idle period of a rank.

An intuitive power-down policy is the *time-out power-down* policy [19]. The time-out power-down policy turns off a rank once it is idle for a pre-defined, fixed period of cycles, regardless of the upcoming command pattern. This results in inflexible power mode transitions, which may turn off the DRAM ranks even during a short idle period or waste active standby power waiting for the timer to expire. Therefore, the time-out power-down policy does not guarantee an acceptable power reduction and may harm the system performance dramatically [20]. Besides the time-out power-down policy, *queue-aware power-down* policy is proposed [21]. In the queue-aware power-down policy, if a rank is idle, commands in the memory controller are checked to see if any of the pending commands is destined for the idle rank. If there is no pending commands heading to the idle rank, it is turned off. The aggressive

bandwidth-neutral strategy proposed in [22] is a policy derived from the queue-aware powerdown policy with an additional snooping mechanism that turns the idle ranks back on upon receiving a memory command in the memory controller. The queue-aware power-down policy and the aggressive bandwidth-neutral strategy do not affect the system performance as much as the time-out power-down policy does, but their effect on reduction DRAM power is limited because they do not maximize the ability of the memory controller.

The scheduling policies are also known as schedulers. Some schedulers stress on scheduling both request commands and internal commands [9][23][24]. These schedulers require extra hardware to allow the memory controller arranges all the commands more sophisticatedly to reduce the DRAM power. Other schedulers focus on scheduling only the request commands. Since the memory controller reorders request commands while preventing data hazards even when no power management policy is employed, scheduling request commands does not add extra hardware to the memory controller. Among this type of schedulers, the *power-aware memory scheduler* is proposed in [21]. The power-aware memory scheduler clusters memory commands destined for the same rank together. While the memory concentrates on accessing one rank, other ranks can be switched to the low power mode to save power. Since only a single rank is activated at a time, other ranks stay in the low power mode for longer periods.

The throttling-based policies restricts memory access commands to be issued to the DIMMs to reduce the DRAM power [21][25]. The *memory throttling* mechanism proposed in [21] increases the power saving by blocking memory commands in the memory controller and force the DRAM chips to stay idle. No command is issued by the memory controller before it has blocked commands for a fixed period of cycles. This fixed period of cycles is called the *throttle delay* (t_{TD}).

With the queue-aware power-down policy, power-aware scheduler and the memory throttling mechanism, the previous work [21] achieves a power saving closed to time-out

power-down policy with a moderate system performance degradation. However, the previous work [21] does not take into consideration that read requests are more critical for the system performance than write requests [26]. In modern multi-core systems, a higher write latency can be tolerated using buffers [27]. Therefore, slowing down the write accesses does not impact the system performance much. Utilizing this fact, one can further reduce DRAM power consumption with a slight system performance overhead.

This thesis chooses to add new techniques based on the power-aware scheduler and the memory throttling mechanism proposed in the previous work [21]. However, all of the related works mentioned above are orthogonal to each other and can be integrated with the proposed



1.4 Our Contributions

To reduce DRAM power consumption, this thesis proposes the read-write aware DRAM scheduling, which utilizes the different criticalities between read accesses and write accesses. The DRAM scheduling mentioned in the remainder of this thesis refers to reordering the sequence of all the memory commands inside the memory controller. In this thesis, the internal DRAM commands such as ACT and PRE...etc. remain their default order and are not taken into consideration in the proposed techniques.

This thesis proposes two techniques, the *read-write aware throttling* mechanism and the *rank level read-write reordering* technique. The read-write aware throttling mechanism effectively cuts down DRAM power consumption. The rank level read-write reordering is employed to significantly reduces the system performance degradation caused by DRAM power management while maintaining the power saving. Our work reduces 75.34% of the DRAM power from the DRAM with no power management. When compared to the existing work, the proposed techniques reduce 10% more DRAM power with less performance degradation. Moreover, by evaluating and comparing with an oracle policy, the experimental results have shown that our work can reduce more power at the expense of a slight system performance degradation.

The remainder of this thesis is organized as follows. The next chapter describes the problem formulation. Chapter 3 places the proposed techniques. The experiment results are presented in Chapter 4. Finally, this thesis is concluded in Chapter 5.

Chapter 2 Problem Description

2.1 System Model

As shown in Fig. 4, the system has one or more processor cores. These cores are connected to a multi-level cache and are equipped with write buffers. A JEDEC standard DRAM is used as a shared main memory for all cores. The DRAM main memory is connected to the last level cache. The DRAM communicates with the processors through a memory controller, which lies between the last level cache and the DRAM circuit. The memory controller receives memory commands from the processors and issues these commands to the DIMMs inside the DRAM. Each memory command contains information including its target address and access type. The memory controller keeps track of the time it receives each command.



Fig. 4 System hierarchy diagram and the architecture of queues inside the memory controller.

Within the memory controller, there are two queues: the *reorder queue* (RQ) and the *command queues* (CQs). Memory access commands from the last level cache are first stored in the RQ. These commands are mapped to certain DRAM ranks and banks according to their target addresses. A scheduler inside the RQ is able to reorder the commands in the RQ while keeping the data hazard-free. After mapping and reordering, the memory controller sends the memory commands from the RQ to the CQs one at a cycle. Each CQ corresponds to a certain rank. Therefore, for a DRAM with n ranks, there are n CQs inside the memory controller. Memory commands destined for rank 1, rank 2... rank n are sent to CQ₁, CQ₂... and CQ_n, respectively. A CQ handles all kinds of commands destined for its corresponding rank. These commands such as ACT, PRE, refresh, power-up, and power-down commands generated by the memory controller. The CQs do not change the order of the memory access commands since they are already reordered by the scheduler inside the RQ. Hence, the CQs issue the commands to the DRAM ranks in a first-in-first-out (FIFO) order.

Normally, the memory controller sends the commands from the RQ to the CQs whenever there are commands in the RQ. When a throttling mechanism is employed, instead of sending the memory access commands from the RQ to the CQs whenever the RQ is not empty, the memory controller blocks commands in the RQ for t_{TD} . No command is sent to the CQs before the throttle delay is reached. When the throttle delay is reached, the memory controller starts sending the blocked commands to the CQs one at a cycle until the RQ is empty. The memory controller repeatedly blocks and releases the commands to realize the throttling mechanism.

Fig. 5 gives an example of how the memory commands are transferred from the RQ to the CQs when the throttling mechanism is employed. In Fig. 5, each rectangle represents a memory command. The access type of each command is denoted by R (read) or W (write), followed by an index number and the target rank of the command. The index numbers are assigned to each memory command according to the time they entered the RQ. The command that enters the RQ

earlier is represented by a smaller index number. For the example shown in Fig. 5, the DRAM is assumed to have four ranks, which are denoted as r_1 , r_2 , r_3 , and r_4 . Correspondingly, there are four CQs in the memory controller. Suppose that the throttle delay is reached at cycle *k*. For simplicity, we denote the *i*th rank as r_i in Fig. 5 as well as in the remainder of this thesis.

As shown in Fig. 5, three commands W1, R2, and W3 are blocked in the RQ during cycle $k - t_{TD}$ to cycle k. When the throttle delay is reached, the RQ starts sending commands from its front to its end. Each memory command is sent to the CQ according to its target rank. Hence, W1 is first sent to the CQ₁, then R2 is sent to the CQ₃, W3 is sent to the CQ₃ at last. Each command in the CQ is issued to the corresponding DRAM rank. CQ₁ issues W1 to r₁ after receiving W1 from the RQ. Since the CQ issues commands in FIFO order, CQ₃ issues R2 to r₃ in advance of W3.





Fig. 5 An example of how the blocked memory commands transfer from the RQ to the CQs when the throttle delay is reached in a throttling mechanism.

The DRAM supports rank level power-mode control. That is, each rank has two different power mode, the active mode and the low power mode. A rank has to be turned on to the active mode before it is able to process the received commands. When a rank is idle, it can be turned off to the low power mode by the memory controller. The memory controller puts power-up and power-down commands into the CQ to switch the power mode of its corresponding DRAM rank. Switching the power mode of a rank is at the cost of transition delays.

The abbreviations and notations used throughout this thesis are listed in the following Table I and Table II.

-		Table I able of abbreviations
	Abbreviation	Definition
	DRAM	dynamic random access memory
	DIMM	dual-in-line memory module
	ACT	activate
2	PRE	precharge
	CKE	clock enable
	PCRAM	phase change random access memory
	RQ	reorder queue
	CQ	command queue
	CQi	the command queue assigned to rank <i>i</i>
	FIFO	first-in-first-out
	\mathbf{r}_{i}	rank <i>i</i>
	RAW	read after write
	MIPS	million instructions per second

Table II Table of notations

Notation	Definition		
P _{PDN}	background power of a DRAM chip in the off mode		
P _{ACT_STBY}	background power of a DRAM chip in the on mode		
P _{REF}	power consumption of refresh operation		
P _{ACT}	power consumption of an ACT command		
P _{PRE}	power consumption of a precharge command		
P _{RD}	average power consumption of read accesses		
P _{WR}	average power consumption of write accesses		
P_{off} total power consumption of a DRAM chip in the off mod			
P_{on} total power consumption of a DRAM chip in the on mo			
t _{PDN}	power down transition delay		
<i>t_{PUP}</i> power up transition delay			
t_{TD} throttle delay			
<i>n</i> number of ranks in the DRAM			
C_{RQ} number of commands in the RQ			
S _i	the <i>i</i> th command set		
C _{Si}	number of commands in the i^{th} command set		
R_i number of read commands in the <i>i</i> th command set			
W_i number of write commands in the <i>i</i> th command set			

2.2 Problem Statement

With the system model described in the previous section, the goal of this thesis is to find a delicate DRAM scheduling scheme that reduces the DRAM power with small system performance degradation for the memory controller. The scheduling scheme includes a throttling mechanism, which controls when the RQ starts sending commands to the CQs. The scheme also contains a scheduling policy for the scheduler inside the RQ, which is able to reorder the sequence of memory request commands in the RQ. The internal commands such as ACT and PRE are not taken into consideration by the scheduler inside the RQ since they are generated and put to the CQs directly by the memory controller. The scheduling policy should guarantee that the reordered sequence of memory commands are hazard-free. Finally, the scheme is in charge of determining when to turn on and off the DRAM ranks.

By using the throttling mechanism, reordering the memory commands and controlling the power mode of ranks, the goal of the proposed scheme is to reduce the power consumption of the DRAM with minor system performance degradation.

Chapter 3 The Proposed Techniques

3.1 Overview

The proposed DRAM power reduction techniques address on lowering DRAM power consumption with slight system performance degradation. Since the proposed techniques are based on the existing policies, this section starts off with the basic and shows the flow chart of the greedy memory controller in Fig. 6.



Fig. 6 Flow chart of a greedy memory controller, which employs the greedy power-down policy.

The greedy memory controller employs the greedy power-down policy, which turns off a DRAM rank whenever it is idle. In the greedy power-down policy, an idle rank is turned off even when there are pending commands destine for it in the RQ. The greedy memory controller does not employ the throttling mechanism. Therefore, whenever the RQ is not empty, a single memory command is sent from the RQ to the corresponding CQ every cycle.

As shown in Fig. 6, at any given cycle, the memory commands from the last level cache are pushed to the end of the RQ. The memory controller checks the state of each rank and turns off the ranks that are idle. After turning off idle ranks, the memory controller send the command at the front of the RQ to its corresponding CQ. Finally, the memory control checks each CQ to see if they are empty. If CQ_i is not empty, the memory controller turns on r_i and issues the commands to it.

Since the greedy memory controller turns off an idle rank regardless of the upcoming memory commands in the RQ, the idle rank is turned off even during a short idle period. This results in frequent power mode transition and leads to dramatic system performance degradation caused by the power mode transition delays [20].

To improve the power reduction and the system performance of the greedy memory controller, the previous work [21] adds the throttling mechanism, the queue-aware power-down policy, and the power-aware memory scheduler to the greedy memory controller. The flow chart of the previous work [21] is shown in Fig. 7.



Fig. 7 Flow chart of the memory controller proposed in the previous work [21].

The light-gray rectangles and decision boxes in Fig. 7 are power reduction techniques added by the previous work [21]. The throttling mechanism, which is shown as the first light-gray decision box in the flow chart, blocks memory commands after they are pushed to the RQ until the throttle delay is reached. The blocked commands are not allowed to be sent to the CQ. When the throttle delay is reached, the memory controller clusters the blocked commands into *command sets* by their target ranks. Commands destined for r_i are clustered into command set

 S_i . The set of commands destined for the same rank as the command that first entered the RQ are moved to the front of the RQ, and so on. The memory controller then checks each command set, if there is command in S_i , all the commands in S_i are allowed to be sent to the CQ. The memory controller then sends command at the front of the RQ to the corresponding CQ. At the end of each cycle, the memory checks each CQ to see if there is commands in it. If CQ_i is empty, the memory controller sends a power-down command to r_i, which turns r_i off.

To sum up, the techniques proposed in the previous work [21] improves both power reduction and system performance from the greedy memory controller. The power-aware memory scheduler in the previous work clusters commands according to their target ranks. This forces the DRAM to concentrate on accessing a certain rank for a period of time, allowing other ranks to be turned off. The queue-aware power-down policy checks the upcoming commands in the CQ before turning off a rank, which prevents a rank to be turned off during a short idle period. When a rank is turned off, the throttling mechanism assures that the rank stays in the low power mode for a long period of time.

However, the previous work [21] does not maximize the capability of the memory controller. Moreover, it does now take into consideration that the read request are more critical to the system performance than the write requests. Utilizing this fact, this thesis proposes the read-write aware throttling and the rank level read-write reordering techniques to modify the previous work [21]. The flow chart of the memory controller that employs the proposed techniques is shown in Fig. 8.



Fig. 8 Flow chart of the memory controller employing the proposed techniques.

Based on the previous work [21], the dark-gray rectangle and box in Fig. 8 are the techniques proposed in this thesis, where the decision box is the *read-write aware throttling* and the rectangle is the *rank level read-write reordering*.

The read-write aware throttling mechanism, which is depicted by the dark-gray decision box, checks for the existence of read commands in each command set. Instead of allowing all the nonempty command sets to be sent to the CQs, only the command sets containing read requests are allowed to be sent to the CQs and only their target ranks are turned on. The other ranks, including ranks with write requests pending in the RQ, stay in the low power mode for another throttle delay to reduce the DRAM power consumption.

The dark-gray rectangle shows that the command sets are reordered by the rank level readwrite reordering before they are sent to the CQs. The read requests in each command set get higher priorities than the write requests. The commands with higher priorities enter the CQs earlier. Since the CQ issues commands to the DIMM in a FIFO order, the read requests reach their target rank as soon as possible. This makes read requests, which are critical to system performance, to be served by the DIMMs earlier and thus the system performance degradation caused by the throttling mechanism is relieved.

For simplicity, the following notations are used in this thesis. Suppose that there are n ranks in the DRAM. There is one RQ and n CQs, $CQ_1, CQ_2 \cdots$ and CQ_n , inside the memory controller. The number of commands blocked inside the RQ is denoted as C_{RQ} . Inside the RQ, commands destined for $r_1, r_2...$ and r_n are clustered into command sets $S_1, S_2, \cdots, and S_n$ respectively. The notation C_{Si} represents the number of commands in the command set S_i . For each command set S_i , R_i denotes the number of read commands, while W_i denotes the number of write commands in it. Therefore, it is clear that we can write the relation between these notations as:

$$C_{RQ} = \sum_{i=1}^{n} C_{Si} = \sum_{i=1}^{n} (R_i + W_i)$$
(3)

Using these notations, the detail of the read-write aware throttling mechanism and the rank level read-write reordering are described in the following sections.

3.2 Read-Write Aware Throttling

The read-write aware throttling mechanism determines if a rank should be turned on whenever the throttle delay is reached. It checks on each command set S_i , which is composed of memory commands destined for r_i in the RQ, to see whether the condition $R_i = 0$ is true. If the condition is satisfied, r_i is turned off and all the commands in S_i remain in the RQ for another throttle delay. On the other hand, if the condition is not satisfied, r_i is turned on and all the commands in S_i are allowed to be sent to CQ_i.

The read-write aware throttling utilizes the fact that read requests affect system performance more than write requests [26]. It is performed on rank level and checks the existence of critical read requests in every command set whenever the throttle delay is reached. If a read request appears in a command set, the memory controller sets the target rank of this command set to *urgent*. Ranks with no pending read requests are set to *trivial*. All the commands destined for an urgent rank are allowed to be sent to the corresponding CQ, while other commands remain in the RQ for another throttle delay. This allows the memory controller to only turn on the urgent ranks and keep the trivial ranks in the low power mode, contributing to a large DRAM power saving.

To better understand how the read-write aware throttling mechanism works, we give a simple example. Suppose that there are four ranks in the DRAM. At a certain point, the throttle delay is reached and the memory commands are blocked inside the RQ, as shown in the left part of Fig. 9. Before sending the commands to the CQs, the commands are first clustered into command sets according to their target ranks. The set of commands destined for the same rank as the command enters the RQ first are reordered to the front. The set of commands destined for the same rank as the command that sits right after the command set at the front is reordered to second to the front, and so on. The order of the commands within the same command set remains the same, the command that enters the RQ earlier is closer to the front of the command

set. The request command sequence after clustering is shown in the right part of Fig. 9, and the pseudo code of clustering command sets is given below Fig. 9. In the pseudo code, the DRAM is assumed to have *n* ranks and cmd_j represents the command in the *j*th slot in the RQ. The action *insert* in line 8 reorders a command to the cmdSetMark[i]th slot and pushes all the commands behind it one slot towards the end of the RQ.



Fig. 9 An example of how commands blocked in the RQ are clustered into command sets.

function ClusterCommandSets():
1. for $l \leftarrow 1$ to n do
2. $cmdSetMark[l] \leftarrow -1$
3. for $j \leftarrow 1$ to C_{RQ} do
4. // Let the target rank of cmd_j be <i>i</i>
5. if $cmdSetMark[i] = -1$ then
6. $cmdSetMark[i] \leftarrow j + 1$
7. else
8. insert cmd_j to $cmdSetMark[i]$
9. for $k \leftarrow 1$ to n do
10. if $cmdSetMark[k] > cmdSetMark[i]$ then
11. $cmdSetMark[k] \leftarrow cmdSetMark[k] + 1$
12. $cmdSetMark[i] \leftarrow cmdSetMark[i] + 1$

From Fig. 9, we can see that:

$$\begin{cases} C_{S1} = 5, R_1 = 1, W_1 = 4 \\ C_{S2} = 1, R_2 = 0, W_2 = 1 \\ C_{S3} = 2, R_3 = 1, W_3 = 1 \\ C_{S4} = 0, R_4 = 0, W_4 = 0 \end{cases}$$

The read-write aware throttling then checks for the command sets containing no read request commands. Since the command set S_4 has no commands in it, its target rank r_4 is considered to be trivial and is turned off to save power. The command set S_2 contains no read requests and thus its target rank r_2 is also considered trivial and is turned off. All the commands inside S_2 are kept blocked in the RQ for another throttle delay. The ranks r_1 and r_3 are considered urgent because there are read requests in S_1 and S_3 . Therefore, commands in S_1 and r_3 to process the commands in S_1 and S_3 .

The pseudo code of the read-write aware throttling, is given as below. The function ReadWriteReorder in line 8 will be explained in the next section.



In implementation, a one-bit register is used for each command set to detect the existence of read commands whenever a new command enters the RQ. Therefore, the complexity of this procedure is lower than the pseudo code since the *if* condition in line 5 in the pseudo code is replaced by the registers.

3.3 Rank Level Read-Write Reordering

The rank level read-write reordering is a scheduling policy for the command sets containing read requests in the RQ. It gives read requests higher priority than write requests. The commands in a command set are sent to the CQ in descending order of priority. Since the CQ issues commands to the DIMM in FIFO order, read requests are issued to the DIMM prior to write requests. This forces the DIMM inside the DRAM to process read requests, which are critical to system performance, as soon as possible. The rank level read-write reordering effectively relieves the system performance degradation caused by the DRAM power management policy.

The system performance degradation is greatly relieved if the read requests are sent to the CQ prior to all the write requests. However, reordering memory commands blindly can lead to a data hazard issue since the memory commands are no longer handled by the DIMM in the same order as the processors sent out. If a read request enters the RQ after a write request and they are both destined for a same address, a read-after-write (RAW) data hazard occurs if the DIMM returns data for this read request prior to the write request. To avoid RAW hazard, the rank level read-write reordering performs a check before reordering. For each read request in the a command set, the rank level read-write reordering checks all the write requests in the same command set that entered the RQ earlier than this read request. If one or more write requests target to the same address as the read request does, they are combined in their original order to form a *command group*. All the command groups are then reordered to preserve the FIFO order of the read request in each command group.

An example is given in Fig. 10, where each rectangle represents a memory command with its access type denoted by W (Write) or R (Read) followed by an index number and the target address of the command. The index numbers are assigned to each memory command according the time they entered the RQ. The command that enters the RQ earlier gets a smaller index number. Fig. 10 illustrates how the commands in a command set S_1 is combined into command groups and reordered.



Fig. 10 An example of how commands in a given command set S₁ are combined into command groups and then reordered.

As shown in Fig. 10, the rank level read-write reordering checks S_1 for read requests. Command R5 is first found, and the rank level read-write reordering search through W1 to W4 to find that W2 and W4 have the same target address as R5. Therefore W2, W4, and R5 and combined into a command group, and the order of these three commands are preserved inside the command group. The rank level read-write reordering then find R6 and W3, which has the same target address as R6. W3 and R6 are thus combined into a command group. Since R5 enters the S_1 before R6, the command group containing R5 is placed in front of the command group containing R6. Commands that are not in any command group are placed in FIFO order behind the last command group.

After combining command groups and reordering, the reordered command sets are sent to the CQs. The target ranks of these command sets are turned on to process these command. It is switched back to the low power mode once all the commands are finished and is kept in the low power mode until the throttle delay is once again reached. The pseudo code of the rank level read-write reordering is given below. In the pseudo code, the command set S_i is assumed to have C_{Si} commands and notations cmd_j and cmd_k represent the j^{th} and k^{th} command in the command set, respectively. Notice that in line 6 and line 9, the action *insert* reorders the command to the *mark*th slot in the command set. For instance, line 6 moves cmd_k to the *mark*th slot and all the commands originally sitting in the *mark*th slot to the $(k - 1)^{\text{th}}$ slot are shifted to $(mark + 1)^{\text{th}}$ slot to k^{th} slot in order.



As shown in the pseudo code, the rank level read-write reordering checks for read requests among all the commands in a command set from the front to the end of the command set. For each read request found, the rank level read-write reordering search through commands that are in front of the read request and do not belong to any command group. All the commands with the same target address as the read request are combined into a command group.

In implementation, the action *insert* is provided by the modern memory controller and no extra hardware is required. The address comparing action in line 5 uses a comparator, whose size differs from 1-bit to the length of the memory address. When a small comparator is used, the rank level read-write reordering is more conservative and tends to insert more write requests

in front of the read requests. The effect on relieving system performance degradation may be slightly weaken if a small comparator is used.



3.4 An Example of The Proposed Policy

In the proposed scheduling policy, the rank level read-write reordering is combined with the read-write aware throttling. To understand how the proposed policy works, a complete example is given as follows. Assume that there are four ranks in the DRAM and the throttle delay is reached at cycle k. Suppose that at cycle k, the command pattern in the RQ is as shown in the left part of Fig. 11. The commands are clustered into command sets according to their target ranks, the result is as shown in the right part of Fig. 11. Notice that the command set S_4 contains no commands and is therefore omitted in Fig. 11.



Fig. 11 An example of how the read-write aware throttling clusters commands in the RQ and determines which ranks should be turned on when the throttle delay is reached.

When the throttle delay is reached at cycle k, the read-write aware throttling is first performed to check on each command set for the existence of read commands. As the result, r_1 and r_3 are considered urgent, while r_2 and r_4 are considered trivial. After the read-write aware throttling, the rank level read-write reordering is performed on command sets S_1 and S_3 before they are sent to CQ₁ and CQ₃. Using S_1 as an example, Fig. 12 shows how the commands in S_1 are reordered and sent to the CQ. The command at the front of the command set has the highest priority while the command at the end has the lowest priority. The commands are sent to the CQ in descending order of priority one at a cycle.



Fig. 12 An example of how the commands in a given command set S_1 are reordered by the rank level read-write reordering and sent to the CQ.

As shown in Fig. 12, rank 1 was originally in the low power mode after all the commands from last throttle period are completed. When the throttle delay is reached and the command set is formed, the rank level read-write reordering checks through the command set and found that W4 and W7 target to the same address as R8. These three commands are then combined to form a command group and reordered to the front of S_1 . Once the reordering completes, the commands are sent to CQ_1 and rank 1 is turned on. Rank 1 is turned off again when all the command finishes. The example shows that the rank level read-write reordering forces the DRAM to process read requests as early as possible.

It is noticeable that for an urgent rank r_i , all the commands in the command set S_i are allowed to be sent to CQ_i . Even the write requests whose target addresses are not identical to any read requests are allowed to be sent to the corresponding CQ instead of kept blocked in the RQ. For example, the target addresses of W1 and W6 in Fig. 12 are not the same as R8, and they are still sent to CQ_1 . The reason is that once a rank is activated, keeping these write requests in the RQ does not contribute to more DRAM power reduction because they will eventually be processed and consumes the same amount of power. Moreover, if these write requests are kept blocked in the RQ until a read requests with the same target address enters the command set, the read request has to wait for these write requests to be completed. This lengthens the latency of the critical read request and has chance to worsen the system performance degradation.



Chapter 4 Experimental Results

This chapter demonstrates and analyzes the experimental results to examine the proposed techniques. First, the simulation environment is described. Second, the evaluation results of how each techniques proposed in this thesis work at certain throttle delay are shown and analyzed. Finally, the evaluation on the power and performance trade-off is carried out and the results are analyzed and compared with other works.

4.1 Simulation Environment

The performance of our work is evaluated with Multi2Sim [28], a widely used cycleaccurate system simulator. Multi2Sim provides detailed simulation of single core or multicore processors and gives us the statistics of the system performance. Our evaluation integrates DRAMSim2 [29] into Multi2Sim to obtain more accurate statistics of DRAM, such as the latency of each memory command, DRAM power consumption and power mode transition delays. DRAMSim2 is a cycle-accurate, JEDEC DDRx memory system simulator, which models the memory controller, memory channels, DRAM ranks, and banks. In an evaluation, Multi2Sim runs the benchmark and generates memory commands accordingly. The memory commands are sent to DRAMSim2 and processed by the DRAM that DRAMSim2 models. The evaluation results of Multi2Sim provide the system throughput statistics, while the evaluation results of DRAMSim2 provide the DRAM power consumption.

The baseline system in the simulations uses the ARM Coretex-A9 MPCore [30]. The configuration parameters of ARM Coretex-A9 MPCore are listed in Table III. The baseline system has two-level caches. In order to evaluate our work by comparing to the previous work

[21], our simulations use the same cache sizes as in the previous work. The detail parameters of the memory system are presented in Table IV. The main memory used in the evaluation is a DDR2 SDRAM, which is one of the JEDEC standard memory available on market [12].

Configuration parameters of ARM Cortex A9 [30]				
Parameter	Value			
Number of cores	4			
Number of threads per core				
Technology node	40 nm			
Operating frequency	2.132 GHz			
Supply voltage	0.66 V			
Threshold voltage	0.23 V			
Decode width	2.1			
Issue width	40 =			
Commit width	4			
Number of arithmetic logic units per core	3			
Number of multipliers per core	896 1/2			
Number of floating-point units per core				
Branch predictor 2 level, 1024-set 2-way BTB				

 Table III

 Configuration parameters of ARM Cortex A9 [30]

Parameter	Value		
Size of level 1 data cache per core	32 KB		
Set associativity of level 1 data cache per core	4-way		
Size of level 1 instruction cache	64 KB		
Set associativity of level 1 instruction cache per core	2-way		
Size of level 2 cache	2 MB		
Set associativity of level 2 cache	8-way		
DRAM frequency	533 MHz		
DRAM frequency Number of DRAM ports	533 MHz 2		
DRAM frequency Number of DRAM ports DRAM device width	533 MHz 2 8		
DRAM frequency Number of DRAM ports DRAM device width Number of DRAM ranks	533 MHz 2 8 4		
DRAM frequency Number of DRAM ports DRAM device width Number of DRAM ranks Number of DRAM banks per rank	533 MHz 2 8 4 4		
DRAM frequency Number of DRAM ports DRAM device width Number of DRAM ranks Number of DRAM banks per rank Number of DRAM rows per bank	533 MHz 2 8 4 4 8192		

Table IV Memory system parameters

Table V

Benchmark combinations of floating-point benchmarks in SPEC CPU2006 [31]

<i>Combination</i>					
fp1	410.bwaves	416.gamess	433.milc	434.zeusmp	
fp2	435.gromacs	436.cactusADM	437.leslie3d	444.namd	
fp3	447.dealII	450.soplex	453.povray	454.calculix	
fp4	459.GemsFDTD	465.tonto	470.1bm	481.wrf	

The workload for our simulations is the SPEC CPU2006 [31] benchmark suite. The benchmarks in the SPEC CPU2006 suite can be separated into integer benchmarks and floating point benchmarks. The floating point benchmarks have higher memory pressure than integer benchmarks and need more sophisticated power management policies [1][21]. Therefore, the benchmarks used in our simulations are randomly chosen from the floating point benchmarks. For each simulation, a benchmark combination containing four benchmarks is used. Every benchmark in the benchmark combination is assigned to a certain core. The benchmark combinations are listed in Table V. Each benchmark combination is run for five million CPU cycles in our evaluation.

Another workload used in the evaluation is the SPLASH-2 benchmarks [32], which are collected from real applications. Using the dynamic context scheduler provided by Multi2Sim [28], each program in the SPLASH-2 benchmarks forks at most four parallel contexts during runtime. The benchmarks in SPLASH-2 used in the evaluation are listed in Table VI.

	Table VI				
SPLASH-2 [32] benchmarks used in the evaluation					
Benchmark Problem size					
Barnes	2048 particles				
Cholesky	tk14.0				
FFT	65536 points				
FMM	2048 particles				
Radix	256k keys, max-value 524288, radix 4096				
	1006				

The SPEC CPU2006 benchmarks are used in section 4.2 and 4.3, and the SPLASH-2 benchmarks are used in section 4.3. In the evaluation, the power consumption is measured in Watts. The system performance is measured in million instructions per second (MIPS), which represents the throughput of the system. All the results are normalized to the *native DRAM*, which refers to the DRAM with no power management policy.

4.2 Analysis on Different Techniques

Although our work employs both the read-write aware throttling and the rank level readwrite reordering, these two techniques can be employed individually. Therefore, the techniques proposed in this thesis are not only evaluated jointly but also separately to see how they affect the DRAM power consumption and the system performance.

In the evaluation, our work is compared to the previous work and an oracle policy. In the oracle policy, the order of the memory accesses is transparent so that the DRAM ranks can be ideally turned on and off when needed. Furthermore, there is no transition delay and transition power in the oracle policy. The power reduction of the oracle policy is the maximum power reduction possible at zero system performance degradation. The oracle policy does not employ any throttling-based mechanism nor reordering. Therefore, the oracle policy can be viewed as a time-out-zero policy, which turns off a rank at the instant it becomes idle, with perfect pre-wakeup capability that turns a rank back on whenever it receives a command.

The benchmark combinations listed in Table V are used in this evaluation. The throttle delay for our work and the previous work is set to 400 CPU cycles, at which both our work and the previous work achieve good power reduction with acceptable system performance degradation. The effect of different throttle delays is analyzed later. The evaluation results of all four benchmark combinations are shown in Fig. 13.





Fig. 13 Power and performance of different policies on different benchmark combinations.

The evaluation results show that when the read-write aware throttling is employed alone, it reduces the DRAM power consumption 10%~15% more than the previous work but causes around 1% more system performance degradation. The reason is that the read-write aware throttling puts a rank into the low power mode until it receives read requests. However, when the rank is turned back on to handle the read requests, there are many write requests waiting to be processed. Without the rank level read-write reordering, the read requests have to wait until all the write requests that enters the queue before them are completed. The system performance is degraded since the critical read requests have to wait for a long time.

On the other hand, when the read-write reordering is used alone with the basic throttling mechanism as in the previous work [21], it improves the system performance by around 1% but the DRAM power consumption remains the same as the previous work [21]. This is because that the rank level read-write reordering only forces the DRAM to process read requests as early as possible and does not create extra power down opportunity.

By combining these two techniques, our work saves 10%~15% more power than the previous work with the same, or even slighter, system performance degradation. More importantly, our work reduces DRAM power consumption to below the oracle solution with 2% of the system performance degradation on average.

The evaluation results show that each technique reacts differently to different benchmark combinations. Since the proposed techniques take into consideration that read requests and write requests are not equally critical to the system performance, the number of requests contained in a benchmark is essential to the effect of the proposed techniques. Therefore, the read requests percentage of each benchmark combination are listed in Table VII. The read requests percentage is obtained by evaluating each benchmark combination with the native DRAM and is calculated by dividing the number of read requests into the total number of memory requests commands.

Read requests percentage of each benchmark combination				
Benchmark combination	Read requests percentage			
fp1	6.76%			
fp2	17.74%			
fp3	55.27%			
fp4	20.14%			

Table VII

Table VII shows that most of the read requests are completed in the cache, and the read requests that send down to the DRAM is less than write requests. It is obvious that fp3 is the most read intensive benchmark combination, while the fp1 is the least read intensive one. The read intensity of different benchmark combination reflects on the power reduction in the evaluation results. The read-write aware throttling works very well on fp1, which has a weak read intensity, due to the fact that most of the time there are only write requests blocked in the RQ and DRAM ranks can be turned off. On the other hand, the strong read intensity of fp3 limits the effect of the read-write aware throttling since it is less likely for a rank to only receive write request in a throttle period and thus cannot be turned off. Nevertheless, our work still manages to save 5% more DRAM power consumption with slightly better system performance than the previous work [21].

As mentioned in section 1.2, the DRAM power can be partitioned into several parts, including background power, active power, precharge power, read power, write power, and the refresh power. To further analyze the evaluation results, Fig. 14 shows these detail power consumptions obtained from the evaluation and compare them to the power consumption of the native DRAM. In Fig. 14, the ACT/PRE power consumption represents the sum of active power and precharge power, while the Read/write burst power represents the sumation of read power and write power. Notice that the refresh power is omitted because the DRAM is refreshed

periodically and the evaluation runs the benchmark for a fixed CPU cycle period, the refresh

power consumptions for different techniques are the same.







(c) Read/write burst power consumptions of different techniques

Fig. 14 The background power, ACT/PRE power, and the read/write power consumptions of different techniques.

The results in Fig. 14 show that the DRAM power consumption is dominated by the background power since the main memory accesses are sparse in the evaluation. Therefore, the throttling-based mechanism is used to turn off idle ranks, and the background power consumption of DRAM is greatly reduced. In addition, the read-write aware throttling creates longer idle period for a rank to be turned off and thus reduces 10%~45% more of the background power against the previous work [21]. The ACT/PRE power consumptions and the read/write burst power consumptions show that the read-write aware throttling cuts down the number of returned commands because the DRAM ranks are in the low power mode for a long period. However, when the read-write aware throttling releases the blocked commands from the RQ to the CQ, it forces the DRAM to focus on accessing the active rank.

It is noticeable that the read/write burst power consumption of our work on fp1 is low. It is because that fp1 has a weak read intensity. When the memory controller finally receives a

read request and turns on a rank, there are many pending write requests targeting that rank, which are blocked by the read-write aware throttling. As the result, in a command group formed by rank level read-write reordering, there are many write requests in front of the read request. Once the rank is activated, it takes a long time processing the pending write requests before it becomes available to process the critical read request. The system performance is thus harmed and fewer main memory commands are completed within the same simulation period. Therefore, the read/write burst power consumption is lower than other techniques.



4.3 Power and Performance Trade-Off

In the proposed techniques, the read-write aware throttling mechanism is the main contributor to the DRAM power reduction. For throttling based power reduction mechanisms, the *throttle delay* is critical to both the DRAM power consumption and the system performance. Long throttle delay leads to better power reduction since the DRAM ranks stay in the low power mode for a long period. However, long throttle delay also leads to worse impact on the system performance because all the commands have to wait for a long period before they are processed by the DRAM. On the other hand, short throttle delay allows the DRAM to process memory commands more frequently but it also limits the effectiveness on the power reduction.

In order to see how different throttle delays affect the performance of our work, an evaluation on different throttle delays is carried out. The evaluation uses all benchmark combinations fp1, fp2, fp3 and fp4. Since every benchmark combination has a different memory command pattern, we averaged the evaluation results of all four benchmark combinations. The average simulation results are shown in Table VIII. All the throttle delays are in CPU cycles. The improvements are the differences between our work and the previous work [21].

	Power reduction percentage		System performance overhead			
Throttle Delay	Previous work [21]	Our work	Improvement	Previous work [21]	Our work	Improvement
100	64.67%	75.46%	10.79%	1.03%	0.61%	0.42%
200	64.54%	75.26%	10.72%	0.87%	0.72%	0.15%
400	64.58%	75.10%	10.52%	1.98%	1.73%	0.25%
800	65.32%	75.14%	9.82%	5.03%	4.88%	0.15%
1600	65.49%	74.96%	9.47%	6.46%	6.39%	0.07%
3200	68.24%	75.17%	6.93%	7.63%	7.46%	0.17%
6400	71.02%	75.42%	4.40%	7.92%	7.88%	0.04%

Table VIII Effect of different throttle delays

The evaluation results show that our work is stable with different throttle delays. It steadily reduces around 75% of DRAM power consumption, which is an upper bound of power reduction, and is around 10% better than the previous work. Moreover, the system performance degradation of our work is slightly better than the previous work. This shows that the read-write aware reordering mechanism effectively relieves the impact on the system performance. The evaluation results also shows as the throttle delay increases, the difference in power reduction between our work and the previous work gets smaller. It is because that when the throttle delay is too large, all the DRAM ranks are in the low power mode for most of the time. Therefore the power consumption is low and the performance degradation is dramatic.

With the results in Table VIII, we can further illustrates the trade-off characteristic between power and performance. By varying the throttle delay, the evaluation shows how our work reacts to different system performance degradations. The average results of all benchmark combinations are shown in Fig. 15, where both the power and performance are normalized to the DRAM with no power management policy. The result shows that our work has a better power and performance trade-off characteristic. Under the same system performance degradation, our work reduces around 10% more of DRAM power than the previous work.





It is noticeable that our work, unlike the previous work [21], is sensitive to the memory command patterns of benchmarks. To show the difference, the evaluation results of benchmark combinations fp1 and fp3 are shown in Fig. 16 and Fig. 17 respectively. The number of read requests is much larger than write requests in fp3, while write requests dominates over read requests in fp1.



Fig. 17 Power and performance trade-off characteristics for fp3.

The trade-off curves of the previous work [21] in Fig. 16 and Fig. 17 have similar slopes. On the other hand, the slope of trade-off curves of our work are different for fp1 and fp3. The results show that when the application is more read intensive, our work is able to effectively reduce more power when with a slight more system performance degradation. The reason is that, the read-write aware throttling accumulates write accesses in the RQ until a read access appears. For read intensive applications, only a few write accesses are kept in the RQ by the read-write aware throttling. Therefore, a slight increment in system performance degradation indicates that the throttle delay is greatly lengthened, which also leads to a much better power reduction.

In order to evaluate how our work performs when the context dynamically forks out, the evaluation on the SPLASH-2 benchmarks [32] is carried out and the resulting trade-off curves are shown in Fig. 18. Both the power reduction and the system performance degradation are normalized to the native DRAM. The system performance here is measured by the number of



Fig. 18 Average power and performance trade-off characteristics on SPLASH-2 [32].

The trade-off curves in Fig. 18 show that the difference between our work and the previous work [21] is smaller than the results obtained from running SPEC CPU2006 benchmarks. The reason is that the SPLASH-2 benchmarks are not memory intensive comparing to the SPEC CPU2006 benchmarks. As the result, the DRAM is turned off most of the time during evaluation

for both the previous work [21] and our work. However, our work still achieves higher power reduction under the same system performance. The statistics of main memory requests per million cycles of different benchmark combinations and benchmarks are listed in Table IX to show the memory intenseness.

Main memory requests per minion cycles of different benchmarks							
	Benchmark combinations/	Main memory requests					
	benchmarks	per million cycles					
	fp1	511391.80					
SDEC CDU2006 (21)	fp2	818090.00					
SPEC CP02006 [31]	fp3	31697.60					
	fp4	442664.80					
	cholesky	894.36					
	fft	2196.41					
SPLASH-2 [32]	fmm	271.93					
	radix	801.45					
	barnes	38.60					
EIN	189	5					

Table IXMain memory requests per million cycles of different benchmarks

The detail evaluation results of each benchmark combination are shown in Table X. The improvement section shown in Table X is normalized to the previous work. The detail evaluation results show that for a variety of applications, our work provides a superior power reduction at the cost of a minor system performance degradation.

				-			
Throttle	Previous work [21]		Our w	Our work		Improvement	
delay	Power (Watts)	MIPS	Power (Watts)	MIPS	Power	MIPS	
100	1.5194	1751.8644	0.7952	1748.6664	47.67%	-0.18%	
200	1.5186	1742.9100	0.8070	1745.0420	46.86%	0.12%	
400	1.5060	1725.0012	0.8230	1730.9708	45.36%	0.35%	
800	1.4654	1707.0924	0.8282	1705.3868	43.48%	-0.10%	
1600	1.3687	1664.2392	0.8648	1690.6760	36.81%	1.59%	
3200	1.2401	1662.5336	0.8692	1671.0616	29.91%	0.51%	
6400	1.1081	1658.2696	0.8749	1659.9752	21.04%	0.10%	
	(a) fp1						
					60		

Table X Detail evaluation results on different throttle delays for SPEC CPU2006 [31]

Throttle	Previous work [21]		Previous work [21] Our work		Improvement	
delay	Power (Watts)	MIPS	Power (Watts)	MIPS	Power	MIPS
100	1.1158	2094.9032	0.7973	2134.1320	28.54%	1.87%
200	1.1250	2125.1776	0.8050	2131.3604	28.44%	0.29%
400	1.1288	2107.0556	0.8048	2106.2028	28.71%	-0.04%
800	1.0938	2010.9024	0.7961	2049.7048	27.21%	1.93%
1600	1.0828	2025.6132	0.7952	2029.0244	26.56%	0.17%
3200	1.0446	1998.9632	0.7856	2010.4760	24.80%	0.58%
6400	0.9436	1995.3388	0.7775	1988.9428	17.60%	-0.32%
(b) fp2						

				14 19			
Throttle	Previous work [21]		Our w	Our work		Improvement	
delay	Power (Watts)	MIPS	Power (Watts)	MIPS	Power	MIPS	
100	0.8920	2464.5920	0.8091	2409.1600	9.30%	-2.25%	
200	0.8905	2462.4600	0.8101	2451.8000	9.03%	-0.43%	
400	0.8922	2417.6880	0.8113	2424.0840	9.07%	0.26%	
800	0.8861	2332.4080	0.8105	2328.1440	8.53%	-0.18%	
1600	0.8626	2281.2400	0.8018	2276.9760	7.05%	-0.19%	
3200	0.8318	2244.9960	0.7903	2240.7320	4.98%	-0.19%	
6400	0.7977	2221.5440	0.7732	2230.0720	3.08%	0.38%	

(c) fp3

Throttle	Previous work [21]		Our work		Improvement	
delay	Power (Watts)	MIPS	Power (Watts)	MIPS	Power	MIPS
100	1.1234	2067.4004	0.8088	2048.0300	28.01%	-0.94%
200	1.1332	2076.3548	0.8153	2083.6036	28.05%	0.35%
400	1.1350	2041.8164	0.8194	2035.5424	27.80%	-0.31%
800	1.1177	1989.7956	0.8204	1980.8412	26.59%	-0.45%
1600	1.0923	1948.2216	0.8177	1940.5464	25.14%	-0.39%
3200	1.0551	1917.3076	0.8079	1910.2720	23.42%	-0.37%
6400	0.9556	1914.5360	0.7955	1914.5360	16.75%	0.00%

(d) fp4

Table XI								
10	Detail evaluation results on different throttle delays for SPLASH-2 [32]							
Throttle	Previous v	work [21]	Our w	vork	Improvement			
delay	Power (Watts)	Cycles	Power (Watts)	Cycles	Power	Cycles		
100	0.86591	386216401	0.80595	383973995	6.92%	0.58%		
200	0.86641	386747351	0.80678	382694644	<mark>6.88%</mark>	1.05%		
400	0.86339	390881890	0.80490	384898787	6.77%	1.53%		
800	0.85677	394132765	0.80304	390673931	<mark>6</mark> .27%	0.88%		
1600	0.84823	398198400	0.79715	396053325	6.02%	0.54%		
3200	0.82893	398909581	0.78876	398746298	4.85%	0.04%		
6400	0.80316	400814358	0.77917	399440076	2.99%	0.34%		

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(a) cholesky

Throttle	Previous work [21]		Our work		Improvement	
delay	Power (Watts)	Cycles	Power (Watts)	Cycles	Power	Cycles
100	1.18733	1626732828	1.06719	1599358623	10.12%	1.68%
200	1.18243	1646152322	1.06244	1613998522	10.15%	1.95%
400	1.17409	1680569237	1.06071	1630723965	9.66%	2.97%
800	1.15385	1728206075	1.05251	1677411431	8.78%	2.94%
1600	1.11851	1783437872	1.03031	1740400454	7.89%	2.41%
3200	1.03481	1785862617	0.97675	1769778925	5.61%	0.90%
6400	0.97555	1793418974	0.94211	1781048450	3.43%	0.69%

Throttle	Previous work [21]		Our work		Improvement	
delay	Power (Watts)	Cycles	Power (Watts)	Cycles	Power	Cycles
100	0.70985	1140576902	0.69463	1138116645	2.14%	0.22%
200	0.70761	1144003008	0.69385	1139193870	1.94%	0.42%
400	0.70981	1149568000	0.69341	1141876406	2.31%	0.67%
800	0.70855	1151543397	0.69405	1150034077	2.05%	0.13%
1600	0.70548	1159231177	0.69312	1154615545	1.75%	0.40%
3200	0.70202	1158699823	0.68899	1160365744	1.86%	-0.14%
6400	0.6924	1161981653	0.68676	1159341940	0.81%	0.23%
(c) fmm						
					0	

Throttle	Previous work [21]		Our work		Improvement	
delay	Power (Watts)	Cycles	Power (Watts)	Cycles	Power	Cycles
100	0.83416	567929757	0.79279	561936504	4.96%	1.06%
200	0.83118	569758770	0.79116	563959080	4.81%	1.02%
400	0.82504	575787691	0.78821	568383335	4.46%	1.29%
800	0.82154	591603316	0.78341	584040811	4.64%	1.28%
1600	0.81879	592267385	0.77909	581449146	4.85%	1.83%
3200	0.80244	596695273	0.76463	595039745	4.71%	0.28%
6400	0.77625	592663748	0.75247	597326751	3.06%	-0.79%

(d) radix

			(u) raura		5	
Throttle	Previous work [21]		Our w	vork	Improvement	
delay	Power (Watts)	Cycles	Power (Watts)	Cycles	Power	Cycles
100	0.65358	1146352684	0.65019	1146958803	0.52%	-0.05%
200	0.65372	1146377562	0.65036	1145273539	0.51%	0.10%
400	0.65382	1146687597	0.6501	1143846545	0.57%	0.25%
800	0.65412	1146328710	0.64973	1145234276	0.67%	0.10%
1600	0.65343	1145896274	0.64998	1147168394	0.53%	-0.11%
3200	0.65286	1146058867	0.64953	1148778795	0.51%	-0.24%
6400	0.65252	1147747030	0.64993	1146213644	0.40%	0.13%

(e) barnes

Chapter 5 Conclusions and Future Works

This thesis proposes a DRAM scheduling policy to magnificently reduce the power consumption of DRAM. The read-write aware throttling mechanism allows the DRAM ranks to stay in the low power mode for a longer period of cycles. It improves the power saving by 10%~15% on average. The rank level read-write reordering forces DRAM to handle read requests, which are critical to the system performance, as soon as it can. It reduces the system performance degradation caused by the power management without sacrificing much power saving. From the experiments, our work reduces the DRAM power consumption by around 75%, which is better than the previous work and the oracle solution. Meanwhile, it causes only 1%~3% system performance degradation, which is smaller than the existing power management policy.

As for the future, we will add a controller that dynamically adjust the throttle delay in runtime to relieve the system performance degradation. We will also explore the potential of combining the techniques proposed in this thesis with other related works such as the automatic data migration, which creates empty ranks that can be shut off until the throttle delay is reached. It is possible to implement our work on the hybrid main memories such as the cached DRAM, which decreases DRAM access and therefore reduces more power. Our work can also be improved by working with the write combining technique, which combines write requests at the last level cache. Furthermore, we will extend this work by utilizing the multiple low power modes provided by the most recent DRAM circuits.

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